

Silicon NPN Power Transistors

2SD546

DESCRIPTION

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- With TO-66 package
- High breakdown voltage

APPLICATIONS

- Converters
- Inverters
- Switching regulators

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

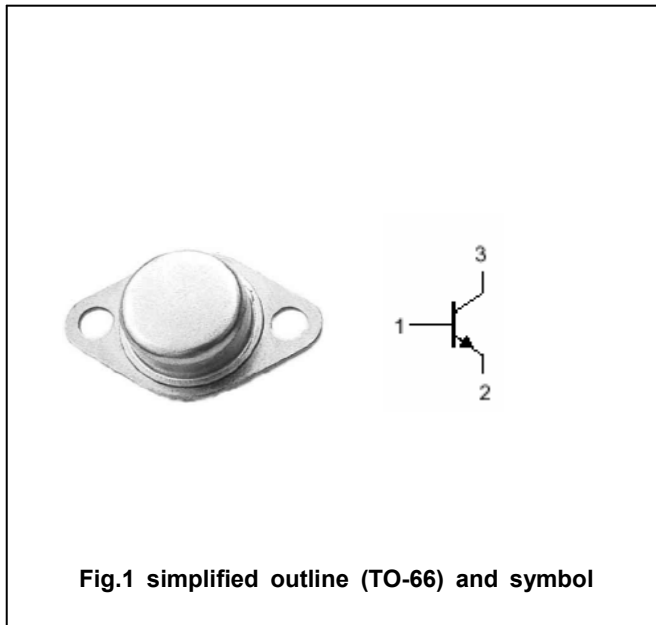


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	800	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		1	A
P _C	Collector power dissipation	T _C =25□	30	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=30\text{mA}; I_B=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=500\text{mA}; I_B=100\text{mA}$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=500\text{mA}; I_B=100\text{mA}$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6\text{V}; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=20\text{mA}; V_{CE}=10\text{V}$	40		200	
f_T	Transition frequency	$I_C=0.1\text{A}; V_{CE}=10\text{V}$		7		MHz

PACKAGE OUTLINE

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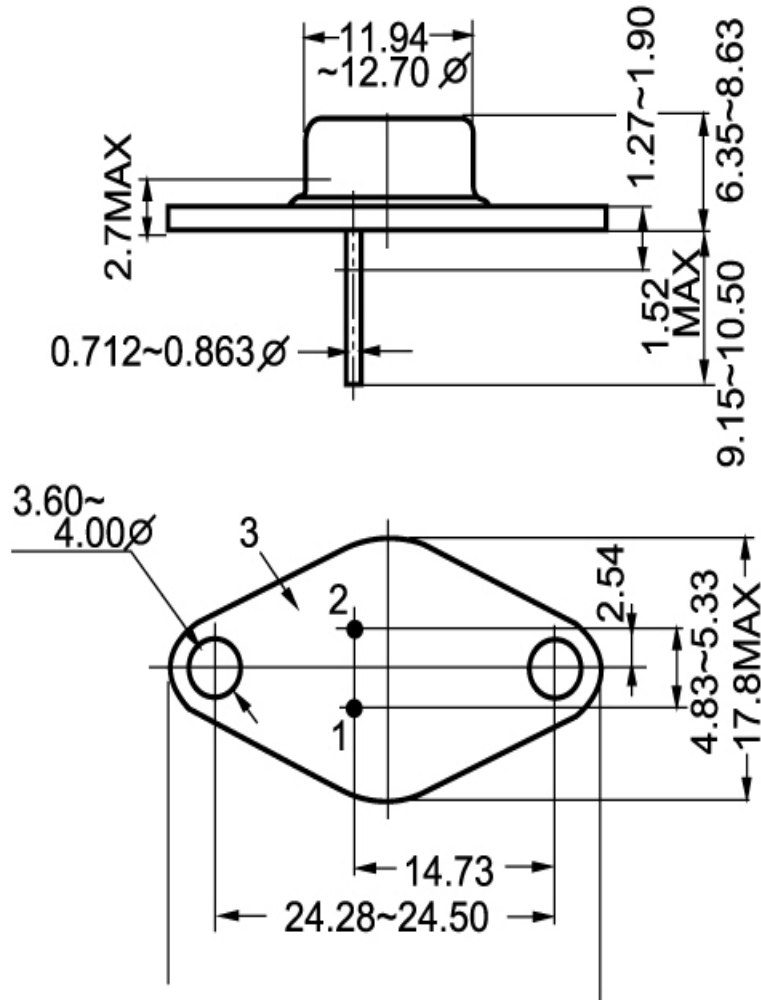


Fig.2 outline dimensions